

FIG. 1

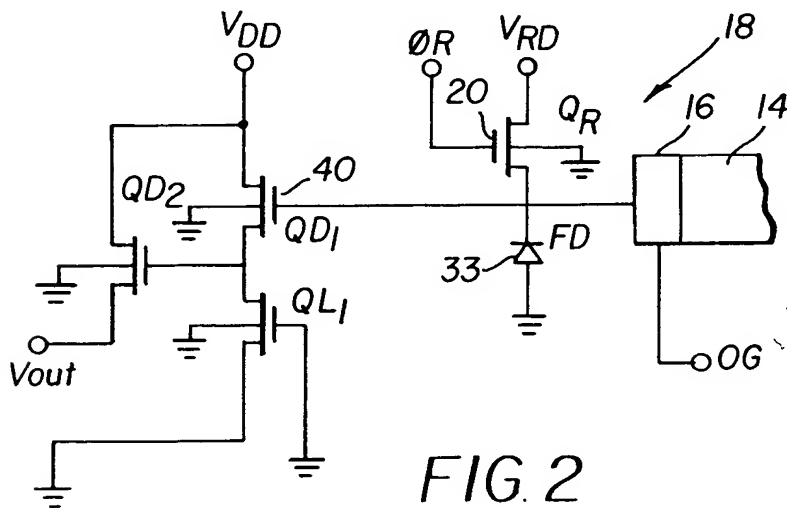


FIG. 2

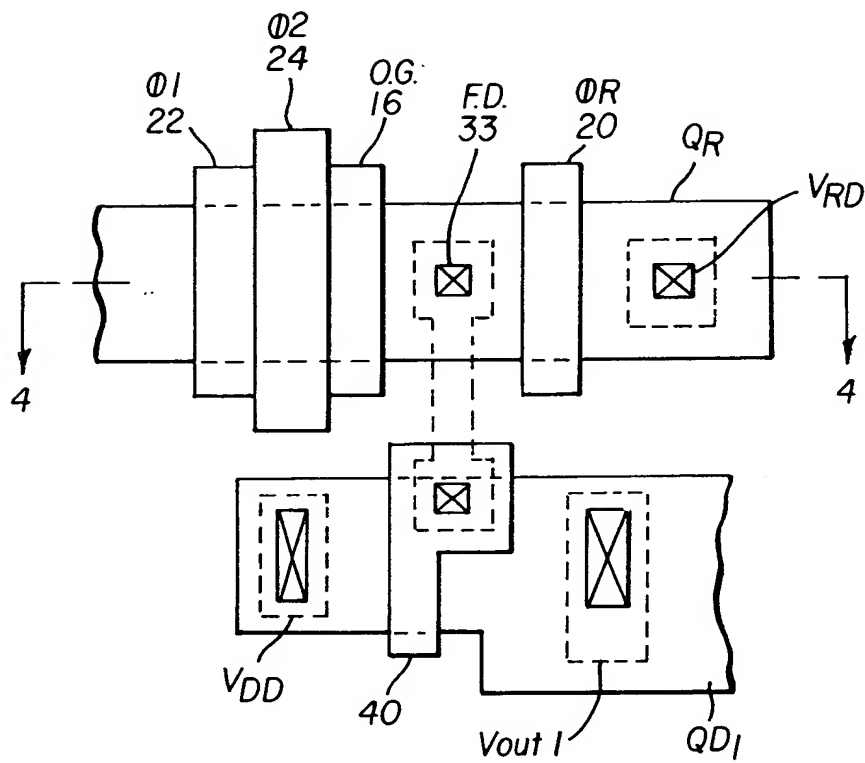


FIG. 3

David N. Nichols, et al.

Diagram illustrating a cross-sectional view of a semiconductor device, likely a MOSFET, showing various regions and layers. The device is built on a p-SUBSTRATE (46). Key components and labels include:

- LOCOS (31)**: Local Oxidation of Silicon region.
- LTO**: Low Temperature Oxide layer.
- n-BURIED CHANNEL (29)**: A channel region buried within the substrate.
- n+ (33) SOURCE**: The source region, labeled as "SOURCE".
- LDD (20) REGION**: Lateral Diffusion Drain region.
- LDS (28) REGION**: Lateral Diffusion Source region.
- CHANNEL REGION (14)**: The channel region, labeled as "CHANNEL REGION".
- QR (26)**: A region labeled "QR".
- p+ (46)**: A heavily doped p-region.
- VRD, DR, OG, D2, D1**: Various gates or electrodes, each associated with a voltage or signal.
- 16, 22, 24, 30, 32**: Other structural or electrical labels.

FIG. 4